NCE N-Channel Super Trench Power MOSFET

Description

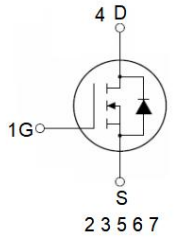
The NCEP40T35AVD uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.

Application

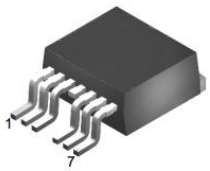
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =40V,I_D =480A (Silicon Limited)
  $R_{DS(ON)}$=0.68mΩ (typical) @ V_{GS}=10V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested
- 100% ΔVds tested



Schematic diagram



TO-263-7L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40T35AVD	NCEP40T35AVD	TO-263-7L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous(Silicon Limited)(Note 1)	I_D	480	A
Drain Current-Continuous(Silicon Limited)(Note 1)	I_D (100℃)	343	A
Drain Current-Continuous(Package Limited)	I_D	350	A
Pulsed Drain Current	I_{DM}	1400	A
Maximum Power Dissipation	P_D	380	W
Derating factor		2.53	W/℃
Single pulse avalanche energy (Note 2)	E_{AS}	3000	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	0.39	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	43	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2.0	3.0	4.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A	-	0.68	0.88	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=20A	100	-	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=20V,V_{GS}=0V, F=1.0MHz	-	12850	-	pF
Output Capacitance	C_{oss}		-	4641	-	pF
Reverse Transfer Capacitance	C_{rss}		-	205	-	pF
Switching Characteristics (Note 1)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=20V,I_D=20A V_{GS}=10V,R_G=1.6Ω	-	26	-	nS
Turn-on Rise Time	t_r		-	14	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	110	-	nS
Turn-Off Fall Time	t_f		-	17	-	nS
Total Gate Charge	Q_g	V_{DS}=20V,I_D=20A, V_{GS}=10V	-	156.5	-	nC
Gate-Source Charge	Q_{gs}		-	59	-	nC
Gate-Drain Charge	Q_{gd}		-	23.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=20A	-	-	1.2	V
Diode Forward Current	I_S		-	-	480	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = I_S di/dt = 100A/μs	-	66	-	nS
Reverse Recovery Charge	Qrr		-	240	-	nC

Notes:

1. Defined by design.Not Subject to production test
2. EAS condition : Tj=25℃,V_{DD}=20V,V_G=10V,L=0.5mH,Rg=25Ω
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

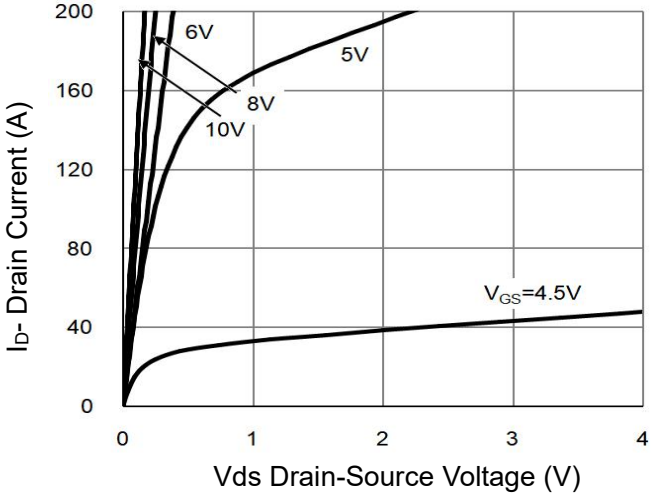


Figure 1 Output Characteristics

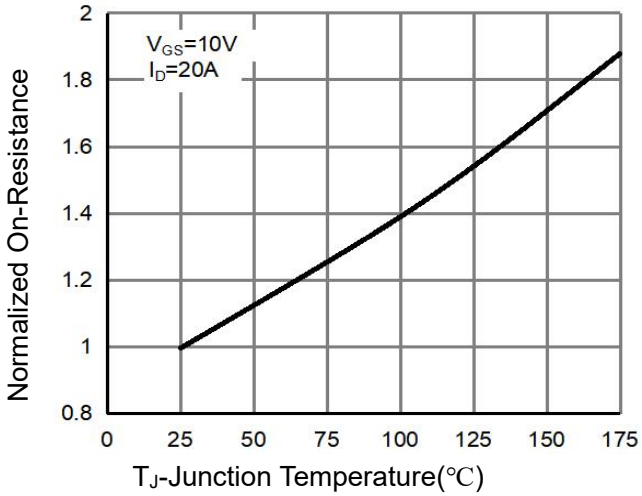


Figure 4 Rdson-Junction Temperature

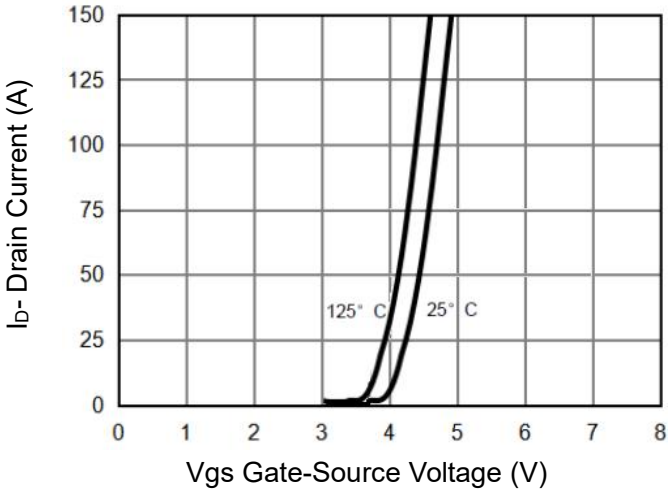


Figure 2 Transfer Characteristics

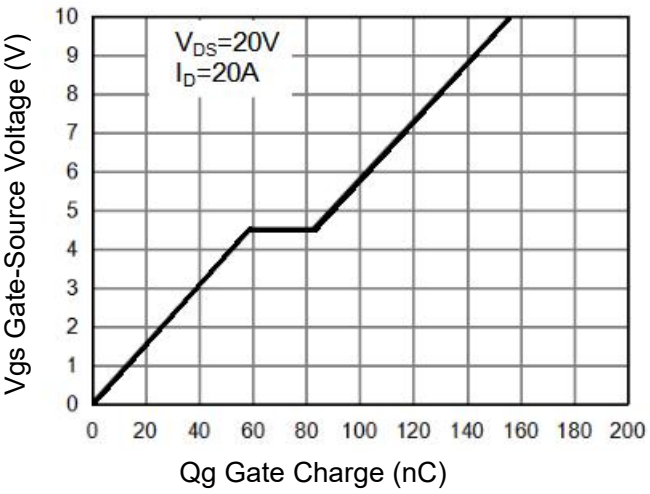


Figure 5 Gate Charge

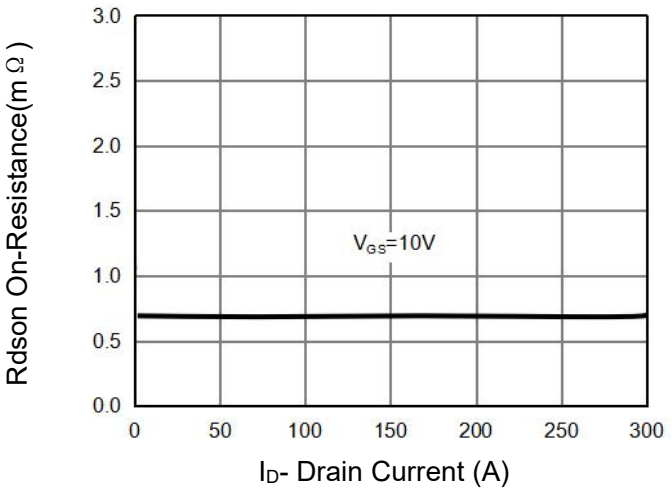


Figure 3 Rdson- Drain Current

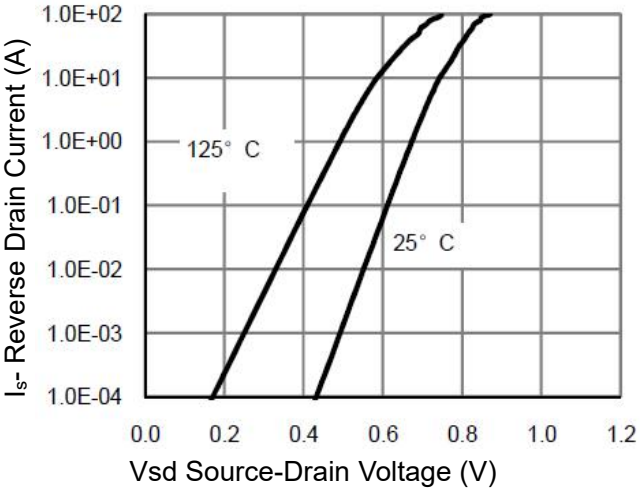


Figure 6 Source- Drain Diode Forward

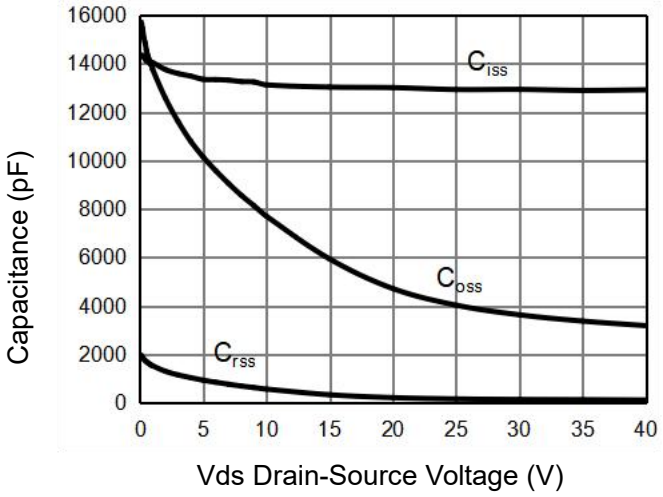


Figure 7 Capacitance vs Vds

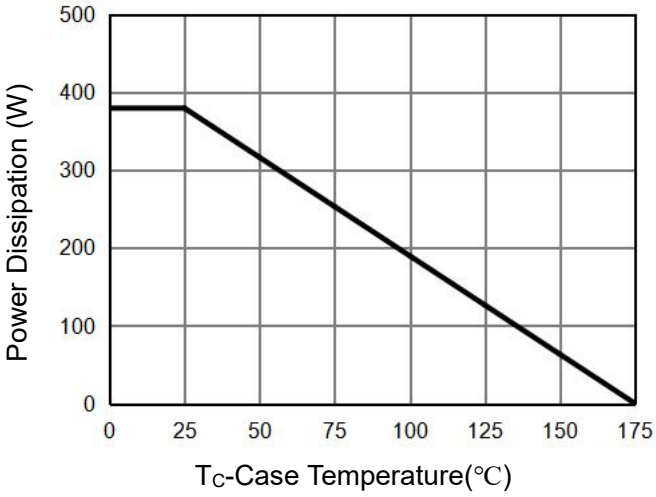


Figure 9 Power De-rating

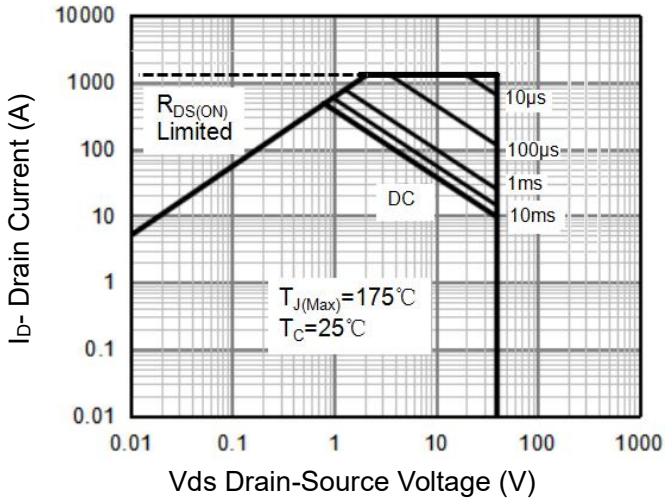


Figure 8 Safe Operation Area(Note 3)

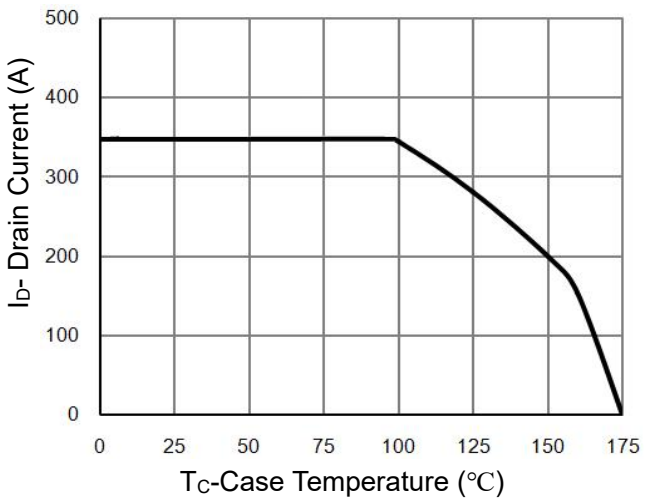


Figure 10 Current De-rating

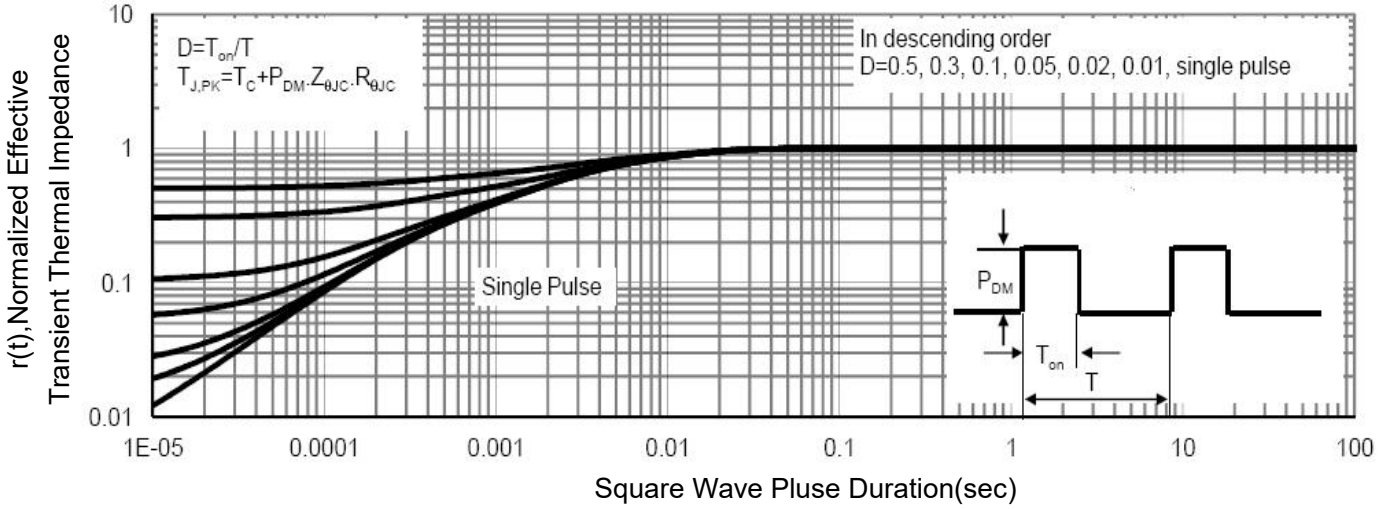
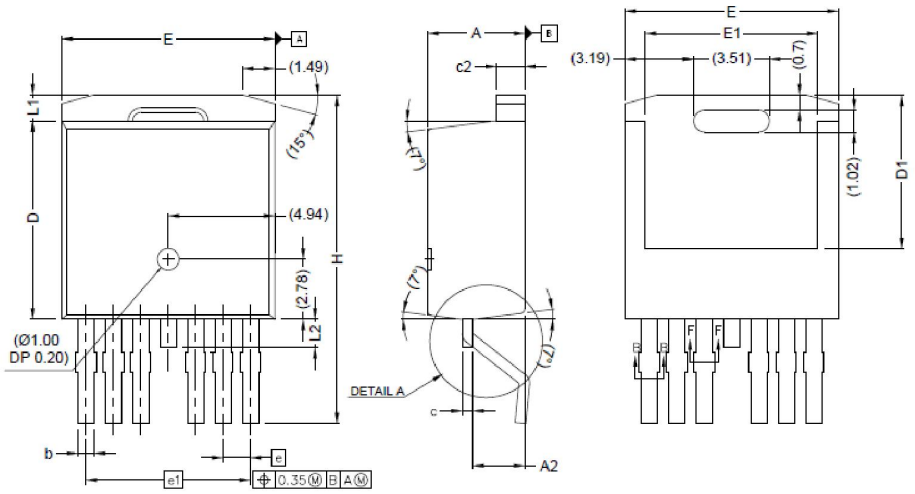
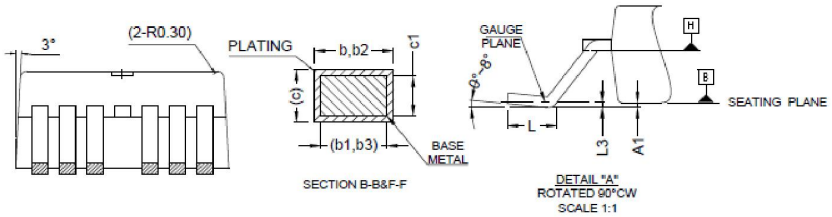


Figure 11 Normalized Maximum Transient Thermal Impedance

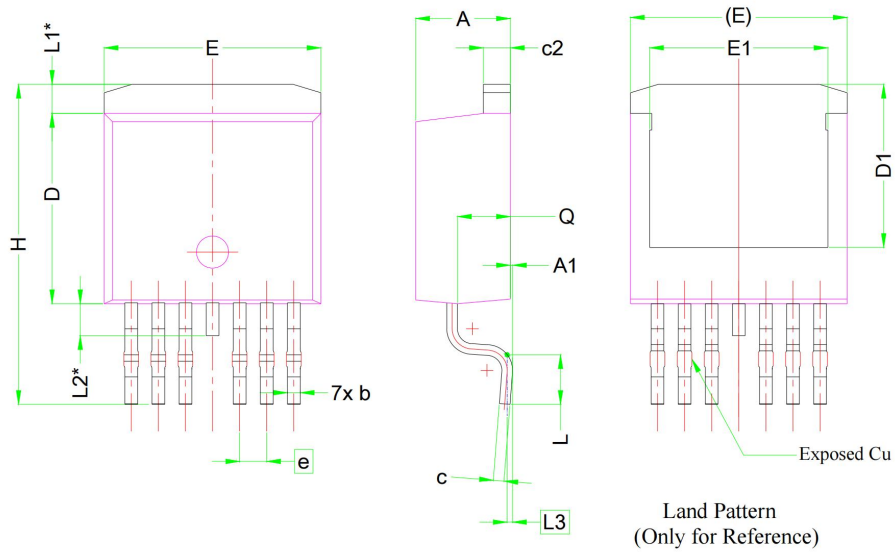
TO-263-7L（B） Package Information

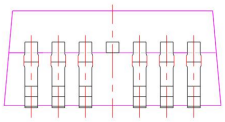




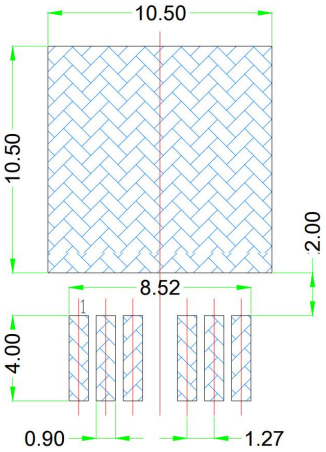
SYMBOL	MIN	MAX
A	4.30	4.70
A1	-	0.25
A2	2.20	2.60
b	0.65	0.85
b1	0.65	0.80
b2	0.80	1.00
b3	0.80	0.95
c	0.45	0.60
c1	0.45	0.55
c2	1.25	1.40
D	9.00	9.40
D1	6.86	7.42
E	9.68	10.08
E1	7.70	8.30
e	1.27 BSC	
e1	7.62 BSC	
L	1.78	2.79
L1	-	1.60
L2	-	1.78
L3	0.25BSC	
H	14.61	15.88

TO-263-7L（G） Package Information





Land Pattern
(Only for Reference)



Note:
1. All Dimensions Are In mm.
2. Dimension D & E Do Not Include Mold Flash.
   Mold Flash Shall Not Exceed 0.127mm Pre Side.
   These Dimensions Are Measured At The Outermost
   Extreme Of The Plastic Body.
3. Thermal Pad Contour Optional Within Dimensions E, L1, D1 & E1.
4. Dimension D1 & E1 Establish A Minmum Mounting Surface for
   The Thermal Pad.
5. "*" is reference .

SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	---
E	9.96	10.16	10.36
E1	8.20	8.35	8.50
e	1.27 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70

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